

L Number	Hits	Search Text	DB	Time stamp
1	248166	(silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:39
2	104	capicator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:42
3	127590	(transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:43
4	500125	capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:43
5	22767	((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:44
6	15641	((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor and (via plug hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:45
7	730133	polysilicon poly\$9 polycrystallins	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:47
8	8610	((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:48
9	302791	barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:53
10	16210	((platinumn pt) with (rhodium rh))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:53
11	356	((ruthenium ru) with silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:53
12	5912	(tungsten w) adj4 nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:54

13	2927	((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 07:54
14	226	(((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and ((platinumn pt) with (rhodium rh))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 08:33
15	74	(((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and ((ruthenium ru) with silicide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 08:33
16	386	(((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and ((tungsten w) adj4 nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 08:33
17	35	(((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and ((ruthenium ru) with silicide)) and (((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and ((tungsten w) adj4 nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 08:33

18	16	<p>(((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and ((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and ((ruthenium ru) with silicide))) and ((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and ((ruthenium ru) with silicide))) and ((tungsten w) adj4 nitride))) and ((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and ((platinum pt) with (rhodium rh))))</p>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 08:34
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23	258	(((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (bipolar (bi adj polar))) and "110"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 08:36
24	4	(((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (bipolar (bi adj polar))) and ((ruthenium ru) with silicide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 08:36
25	17	(((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (bipolar (bi adj polar))) and ((platinum pt) with (rhodium rh))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 08:36
26	4	(((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (bipolar (bi adj polar))) and ((tungsten w) adj4 nitride)) and (((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinum pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (bipolar (bi adj polar))) and ((platinum pt) with (rhodium rh)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 08:36

27	0	(((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (bipolar (bi adj polar))) and ((ruthenium ru) with silicide))) and (((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and ((bipolar (bi adj polar))) and ((tungsten w) adj4 nitride)) and (((((((transistor bipolar (bi adj polar) mosfet mos (metal adj oxide) drain source) and ((silicon si germanium gaas ge ((si silicon) adj4 sapphire)) with substrate)) and capacitor) and (via plug hole)) and (polysilicon poly\$9 polycrystallins)) and (barrier ((platinumn pt) with (rhodium rh)) ((ruthenium ru) with silicide))) and (bipolar (bi adj polar))) and ((platinumn pt) with (rhodium rh)))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 08:36
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